

Observation of a Mott insulating ground state for Sn/Ge(111) at low temperature

R. Cortes,¹ A. Tejeda,² J. Lobo,³ C. Didiot,⁴ B. Kierren,⁴ D. Malterre,⁴ E. G. Michel,⁵ and A. Mascaraque¹¹Dpto. de Física de Materiales, Universidad Complutense de Madrid, 28040 Madrid, Spain²Materiaux et Phénomènes Quantiques, FR CNRS 2437, Université Paris 7, 75251 Paris, France³Physik-Institut, University of Zurich and Swiss Light Source, Paul Scherrer Institut, Switzerland.⁴Laboratoire de Physique des Matériaux, Université Henri Poincaré, 54506 Vandœuvre les Nancy, France⁵Dpto. de Física de la Materia Condensada, Universidad Autónoma de Madrid, 28049 Madrid, Spain

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We report an investigation on the properties of 0.33 ML of Sn on Ge(111) at temperatures down to 5 K. Low-energy electron diffraction and scanning tunneling microscopy show that the $(\sqrt{3} \times \sqrt{3})$ phase formed at 200 K, reverts to a new $(\sqrt{3} \times \sqrt{3})R30$ phase below 30 K. The vertical distortion characteristic of the $(\sqrt{3} \times \sqrt{3})$ phase is lost across the phase transition. Angle-resolved photoemission experiments show that concomitantly with the structural phase transition, a metal-insulator phase transition takes place. In agreement with theoretical predictions, the $(\sqrt{3} \times \sqrt{3})R30$ ground state is interpreted as the experimental realization of a Mott insulator for a narrow half-filled band in a two-dimensional triangular lattice.

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The band theory of crystalline solids is one of the most successful parts of solid state physics. However, exceptions to the predictions of simple band theory are found when the approximation of independent electrons fails, due to electron repulsion effects [1]. This is the case of insulating materials that should be metallic according to band theory. In a simple view, the independent electron approach is not adequate when the kinetic energy (band width) is smaller than the electron-electron interaction (Coulomb energy). The new ground state formed is the so-called Mott insulator [1]. It is characterized by strong electron-electron interactions, which are crucial to understand the behavior of many interesting materials [2].

Semiconductor surfaces present narrow surface bands, and thus are excellent playgrounds to search for Mott insulating phases, and to understand their rich physical behavior. Known examples of Mott insulators of this kind include the surfaces of SiC (0001) [3] and of K/Si(111) [4]. In both cases, the occupation with adatoms of T_4 sites produces a $(\sqrt{3} \times \sqrt{3})R30$ structure ($\sqrt{3}$ in the following), which should exhibit a half-filled surface band, but is indeed insulating. The reconstructions of 0.33 monolayers (ML) of group IV adatoms on Si(111) or Ge(111) are isoelectronic with these systems and also exhibit the same atomic arrangement. Thus, they are good candidates to observe the same kind of behavior [5, 6]. However, at variance with the two cases described above, the structure for both Sn and Pb on Ge(111) below 200 K is a $(\sqrt{3} \times \sqrt{3})$ reconstruction [7, 8]. This phase is metallic [9, 10]. The $(\sqrt{3} \times \sqrt{3})$ unit cell is distorted in a vertical direction because it contains three Sn adatoms and one of them is at a position higher ("up") than the other two ("down"). The different behavior in isoelectronic systems with such a similar atomic arrangement (Mott insulating vs. metallic state), raises exciting issues on the origin of the different ground states found.

In this Letter, we demonstrate that the ground state

of Sn/Ge(111) is a Mott insulating phase of $\sqrt{3} \times \sqrt{3}$ symmetry. We provide a full description of its structural and electronic properties by measuring at temperatures well below the values reached before. We find that below 30 K, the $(\sqrt{3} \times \sqrt{3})$ phase becomes unstable and a new phase of $\sqrt{3} \times \sqrt{3}$ symmetry [11] is formed. The phase transition is fully reversible, and it is due to the disappearance of the $(\sqrt{3} \times \sqrt{3})$ vertical distortion at low temperatures. Concomitantly with the structural phase transition, a band gap opens in the low-temperature, at $\sqrt{3} \times \sqrt{3}$ phase. The Mott insulating phase competes with a metallic, $(\sqrt{3} \times \sqrt{3})$ -distorted state, which is more stable at higher temperatures.

The experiments were carried out in two different ultra-high vacuum chambers, and include angle-resolved photoemission spectroscopy (ARPES), low-energy electron diffraction (LEED), and scanning tunneling microscopy (STM) measurements of 0.33 ML of Sn atoms on Ge(111). These techniques provide complementary information on both the short-range (STM) and long-range (LEED) surface order, and on the electronic structure and the single-particle spectral function (ARPES). The STM apparatus was a low temperature microscope (Omicron), which operated between 4.7 and 300 K. STM images and height profiles shown are neither filtered nor treated, with the exception of the subtraction of a plane. ARPES experiments down to 10 K used a Scienta SES-2002 electron analyzer and synchrotron light from the SIS beam line at the Swiss Light Source [12]. Both chambers were equipped with LEED. The substrate was n-type Ge(111) ($\phi = 0.4$ eV). The preparation of the sample and of the $(\sqrt{3} \times \sqrt{3})$ phase have been described before [9].

A sharp $(\sqrt{3} \times \sqrt{3})$ LEED pattern is observed at 130 K (Fig. 1). Below 30 K, the $(\sqrt{3} \times \sqrt{3})$ superstructure spots weaken and the pattern becomes $\sqrt{3} \times \sqrt{3}$. The new pattern is also sharp and with low background. The phase transition is fully reversible. We refer to this new phase as low-temperature $\sqrt{3} \times \sqrt{3}$ (LT- $\sqrt{3}$) [11].

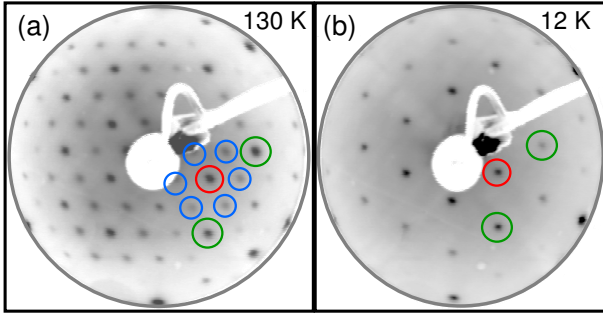


FIG. 1: (Color on line) LEED patterns from (a) the (3×3) and (b) the $\sqrt{3} \times \sqrt{3}$ phase. The primary energy is 94 eV. Circles highlight (1×1) (green), (3×3) (blue), and $\sqrt{3} \times \sqrt{3}$ (red) spots.

Fig. 2 shows $\sqrt{3} \times \sqrt{3}$ led-states representative STM images for the $\sqrt{3} \times \sqrt{3}$ phase. There is an excellent $\sqrt{3} \times \sqrt{3}$ long range order, and only atoms around defects appear brighter, indicating a local pinning to a (3×3) symmetry. To make easier the comparison between the two phases, images of the same size of a $\sqrt{3} \times \sqrt{3}$ and (3×3) surface are also shown. In the latter the larger protrusions correspond to the "up" atom of the reconstruction, and form a hexagonal pattern. The two "down" atoms are resolved and imaged as smaller protrusions.

In order to understand the nature of the $\sqrt{3} \times \sqrt{3}$ phase, the first step is discarding any artifact in the STM images. Such effects have been reported for the low temperature reconstructions of Si(100) [13], Ge(111) [14], and Pb/Ge(111) [15]. In agreement with previous studies on Ge(111) with a similar doping as our sample [14], we find tip-induced band bending effects when the sample is in depletion conditions (i.e. positive sample voltage for our n-doped sample). For negative sample voltages, images were acquired for a variety of measuring conditions. We find no detectable effect of the tip for a range of voltages and tunneling current, from which we select a safe range of reliable measuring conditions of $V = 1.0 - 1.5$ V and $I = 1$ nA. In conclusion, the loss of (3×3) long range order observed in LEED is explained from the disappearance of the atomic vertical distortion of the (3×3) phase, as observed in STM images. These structural modifications are fully reversible going up and down with temperature. Thus, the structure of the $\sqrt{3} \times \sqrt{3}$ phase corresponds to the occupation of equivalent T_4 sites.

This finding is analyzed quantitatively in Fig. 2, which shows a height analysis for both the (3×3) and the $\sqrt{3} \times \sqrt{3}$ phases. Atomic heights are measured for both reconstructions for 250 and 350 atoms, respectively. The results are shown as histograms in Fig. 2. Two different, well defined heights are found for the (3×3) phase. The height difference is 0.65 Å. The height distribution is fit using two gaussian functions. The height of "up" atoms is taken as zero level. An analogous height anal-

ysis for the $\sqrt{3} \times \sqrt{3}$ phase shows that there is a single atomic height, following a gaussian distribution. As mentioned above, atoms at distorted "up" positions survive around defects also for the $\sqrt{3} \times \sqrt{3}$ phase. The location and relative height of these atoms has been monitored across the phase transition. We find that their atomic height does not change, and that they become part of the (3×3) reconstruction, once the phase transition is completed. Thus, their atomic height can be used to compare the atomic heights found for the $\sqrt{3} \times \sqrt{3}$ and the (3×3) phases. Using this method, we find that the atomic height corresponding to the $\sqrt{3} \times \sqrt{3}$ phase is 0.35 Å, between the heights of the "up" and "down" atoms of the (3×3) phase.

A crucial point to understand the nature of the $\sqrt{3} \times \sqrt{3}$ phase is to analyze its electronic structure with ARPES. When ARPES is used to probe metal/semiconductor interfaces, surface photovoltage effects should be taken into account [16]. UV radiation stabilizes a temperature-dependent surface photovoltage, which shifts uniformly both the core levels binding energies and the valence band. As expected for an n-doped sample, the three binding energies probed (Ge 4d, Sn 3d and valence band) shift at low temperature to smaller values (Fig. 3). The saturation of the shift at 30 K for Ge 4d and Sn 3d indicates that "flat band conditions" are reached [17]. This situation corresponds to a complete elimination of the band bending [18]. For temperatures below 30 K, the binding energy of the valence band leading edge deviates from the behavior of the core levels. The energy difference below 15 K is 60 meV. This differential shift is attributed to the opening of a surface band gap [19].

The opening of a surface band gap is confirmed by a detailed analysis with ARPES. Fig. 4 shows the valence band along $[1\bar{1}2]$ direction, which corresponds to $\Gamma_{(3 \times 3)}$, for two different surface temperatures. The data are symmetrized with respect to the Fermi energy following standard practice in ARPES work on the cuprates [20]. In the symmetrized data, the effect of the Fermi function on the temperature dependence of the spectral function is removed. The position of the Fermi energy is corrected by the surface photovoltage, measured from the uniform shift of the Ge 4d and Sn 3d core levels. The Fermi energy thus determined is in perfect agreement with the Fermi edge observed in the metallic (3×3) phase. The same method is used to determine the Fermi energy in the $\sqrt{3} \times \sqrt{3}$ phase. Note the two surface state bands observed in the (3×3) phase, one of them crossing the Fermi energy. The spectral weight closer to the Fermi energy in the (3×3) phase, disappears in the $\sqrt{3} \times \sqrt{3}$ phase, indicating the opening of a surface band gap (Fig. 4). The redistribution of spectral intensity around the Fermi energy affects a range of 0.4 eV below the valence band leading edge. Indeed, the surface state which crossed the Fermi energy in the (3×3) phase is strongly depleted. These changes are again fully reversible with

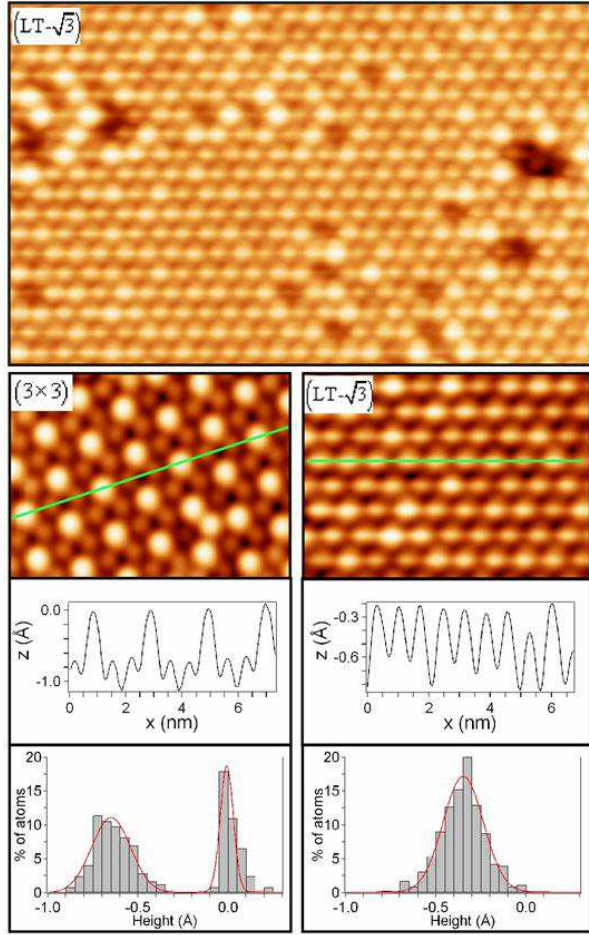


FIG. 2: (Color on line) Top: $18 \times 11 \text{ nm}^2$ STM image ($V = -1.4 \text{ V}$, $I = 1.0 \text{ nA}$, $T = 5 \text{ K}$) of the $\text{LT-}\sqrt{3}$ phase. Bottom: $7 \times 5 \text{ nm}^2$ STM image of the (3×3) ($V = -1.0 \text{ V}$; $I = 1.0 \text{ nA}$, $T = 112 \text{ K}$) phase and $\text{LT-}\sqrt{3}$ ($V = -1.4 \text{ V}$, $I = 1.0 \text{ nA}$, $T = 5 \text{ K}$), respectively. Below we show directly-extracted height profiles corresponding to the direction highlighted in the STM image, and an histogram of the atomic heights found in each case.

temperature.

As shown in Fig. 4, the band gap and the corresponding redistribution of spectral intensity is fairly uniform, and it affects extended areas of reciprocal space. This is typical of a Mott insulator, where the band gap is not related to the surface periodicity but rather to electron repulsion. All these features of the electronic structure are qualitatively consistent with the spectral changes expected for a Mott transition [2, 21, 22]. The stabilization of a charge density wave by the Peierls mechanism would also give rise to a gap opening. However, this possibility can be safely excluded, first because the value of the gap is much larger than the thermal energy at the critical temperature ($k_B T_c$), and second because the gap affects extended areas of reciprocal space and is not related to any nesting vector [23].

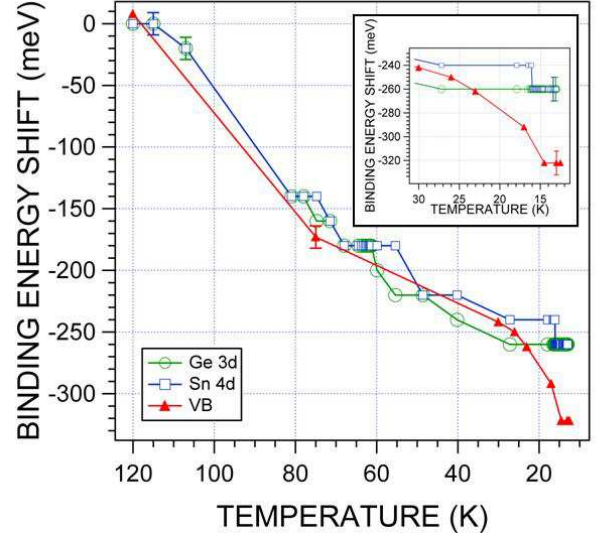


FIG. 3: (Color on line) Binding energy shift of Ge 3d (circles), Sn 3d (squares), and valence band leading edge (filled triangles) vs. temperature. Values at 120 K are taken as a reference. Inset: enlarged view of the behavior for $T < 30 \text{ K}$. Lines are guide to the view.

The observation of a Mott insulating ground state is understood from theoretical calculations performed in the local-density approximation (LDA), which have compared the stability of a $\sqrt{3} \times \sqrt{3}$ vs. a distorted (3×3) structure. The ground state found was the (3×3) phase [9], but the energy difference with respect to a $\sqrt{3} \times \sqrt{3}$ phase was only 5 meV/Sn atom [5]. If electron correlation effects are considered, the energy difference between both phases would be even smaller, and close to the accuracy of the calculation. It was also predicted that a $\sqrt{3} \times \sqrt{3}$ phase should become a Mott insulator [5]. The experiments show that both states are indeed observed. The energetic balance favors the (3×3) distorted metallic state above 30 K, while the insulating, $\sqrt{3} \times \sqrt{3}$ phase is observed below this temperature. The existence of a phase transition indicates that there is a temperature dependent modification of the potential energy landscape. The stability of the (3×3) phase lies on a delicate balance between the electronic energy gained in the new structure and the elastic energy involved in the distortion [24], which affects not only the Sn atoms, but also several layers of the Ge(111) crystal [25]. The elastic response of the lattice is effectively modified in Ge at low temperatures, as demonstrated by the negative lattice expansion and anomalous Grüneisen parameters below

30 K [26]. This modification is due to a change of the phonon modes excited [27]. On the other hand, we may expect that the charge screening is also modified at very low temperatures due to the decrease of the carrier concentration, favoring an increase of the effective electron repulsion. Any of these two effects may be strong enough

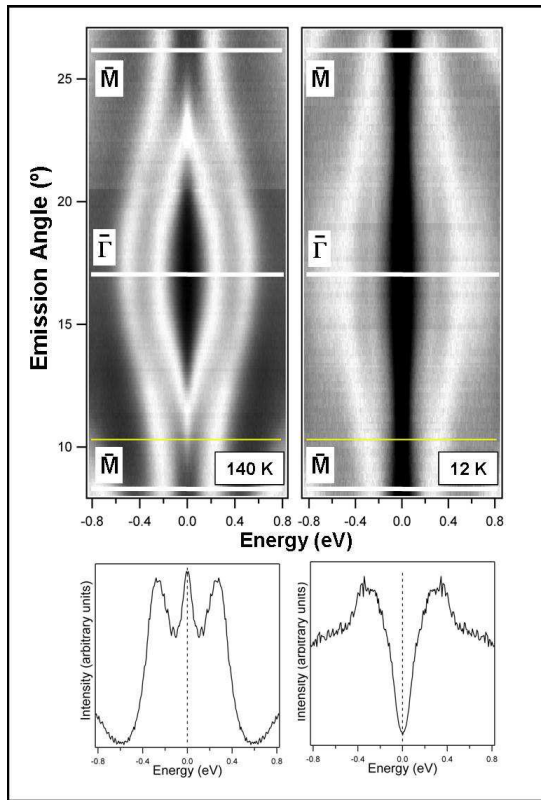


FIG. 4: (Color on line) Top: symmetrized angle-resolved photoemission spectra shown in gray scale (bright color means more intensity), as a function of emission angle along the $[1\bar{1}2]$ direction for both the (3×3) (left) and the $LT-\bar{3}$ (right) phases. Symmetry points correspond to the (3×3) Brillouin zone. Bottom: two selected symmetrized spectra corresponding to the crossing point of the surface state (horizontal yellow line in top panel) at 140 K (left) and 12 K (right). All energy scales are referred to the Fermi energy.

to provoke the phase transition. Further theoretical work is needed to completely solve this question. Note that recent reports provide contradictory evidence on the existence of a glassy-like ground state for $Pb/Ge(111)$ at low temperatures [15, 28]. This disordered state is different from the $\bar{3}$ phase that we report here, which represents a well-ordered structure associated to a metal/insulator transition.

In conclusion, we present experimental evidence for a Mott insulating ground state of $Sn/Ge(111)$. The results of three techniques (LEED, STM, and ARPES), which probe very different surface properties, converge to show that a structural phase transition from a distorted and metallic (3×3) phase to a flat and insulating $LT-\bar{3}$ phase is observed at 25 K. This finding is an indication of a more general phenomenon, which may also be observed in different metal/semiconductor interfaces.

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- [1] F. Gebhard, *The Mott metal-insulator transition* (Springer, New York, 1997).
- [2] M. Imada, A. Fujimori, and Y. Tokura, *Rev. Mod. Phys.* **70**, 1039 (1998); M. Capone et al, *Phys. Rev. Lett.* **93**, 047001 (2004); P. L. Little et al, *Science* **302**, 89 (2003).
- [3] L. I. Johansson, F. Omann, and P. Martensson, *Surf. Sci.* **360**, L478 (1996); J. M. Themlin et al, *Europhys. Lett.* **39**, 61 (1997).
- [4] H. H. W. Eiting et al, *Phys. Rev. Lett.* **78**, 1331 (1997).
- [5] F. Flores et al, *Prog. Surf. Sci.* **67**, 299 (2001).
- [6] G. Santoro, S. Scandolo and E. Tosatti, *Phys. Rev. B* **59**, 1891 (1999).
- [7] J. M. Carpinelli et al, *Nature* **381**, 398 (1996) and *Phys. Rev. Lett.* **79**, 2859 (1997).
- [8] J. Ortega, R. Perez, and F. Flores, *J. Phys. Condens. Matter* **14**, 5979 (2002) and references therein.
- [9] J. Avila et al, *Phys. Rev. Lett.* **82**, 442 (1999).
- [10] R. I. G. Uhrberg and T. Balasubramanian, *Phys. Rev. Lett.* **81**, 2108 (1998).
- [11] A $(3 \times 3)R30$ phase is also observed at room temperature, due to excitation of vertical dynamical fluctuations in the (3×3) distorted structure.
- [12] The energy/angle resolution is 9 meV/0.1°.
- [13] S. Yoshida et al, *Phys. Rev. B* **70**, 235411 (2004) and references therein.
- [14] R. M. Feenstra et al, *Phys. Rev. B* **71**, 125316 (2005).
- [15] I. Brihuega et al, *Phys. Rev. Lett.* **95**, 205102 (2005).
- [16] J. E. Demuth et al, *Phys. Rev. Lett.* **56**, 1408 (1986); M. Alonso, R. Cimino, and K. Horn, *Phys. Rev. Lett.* **64**, 1947 (1990).
- [17] The shift observed at 30 K is the maximum total shift expected, as estimated from sample doping and the change of the chemical potential and of the Ge band gap with temperature.
- [18] E. G. M. Michel et al, *Phys. Rev. B* **45**, 11811 (1992).
- [19] A larger photovoltage for the valence band is discarded, first because the shift detected exceeds the maximum value due to a change of the band bending only, and second because the photon flux used for probing the core levels is larger than for the valence band.
- [20] A. Damascelli, Z. Hussain, and Z. X. Shen, *Rev. Mod. Phys.* **75**, 473 (2003).
- [21] L. Perfetti et al, *Phys. Rev. Lett.* **90**, 166401 (2003).
- [22] X. Y. Zhang, M. J. Rozenberg, and G. Kotliar, *Phys. Rev. Lett.* **70**, 1666 (1993).
- [23] G. G. Giner, *Density Waves in Solids* (Addison-Wesley, Reading, MA, 1994).
- [24] D. Farias et al, *Phys. Rev. Lett.* **91**, 016103 (2003).
- [25] A. Mascaraque et al, *Phys. Rev. Lett.* **82**, 2524 (1999).
- [26] G. Dolling and R. A. Cowley, *Proc. Phys. Soc.* **88**, 463 (1966).
- [27] S. Biemacki and M. Scheer, *Phys. Rev. Lett.* **63**, 290 (1989).
- [28] J. Guo, J. Shi, and E. W. Plummer, *Phys. Rev. Lett.* **94**, 036105 (2005).